onsemi

<u>Diode</u> – Power, Bare Die

Gen VII, Fast Recovery 1200 V, 100 A

PCFF100H120SWF

Features

- Advanced Gen VII Technology
- Fast and Soft Recovery
- Maximum Junction Temperature 175°C
- Low Forward Voltage: $V_F = 1.78 \text{ V} \text{ (Typ.)} @ I_F = 100 \text{ A}$
- Easy to Parallel Operation

Typical Applications

- Solar
- Energy storage
- Industrial motor control

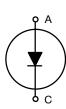
MECHANICAL PARAMETERS

Parameter	Value	Unit		
Die Size (w/ Scribe Lane)	4,200 x 8,400	μm ²		
Anode Pad Size	3,237 x 7,437	μm ²		
Scribe Lane Width	80	μm		
Die Thickness	119	μm		
Top Metal	6 μm AlSiCu			
Back Metal	1.65 μm Ti/NiV/Ag			
Topside Passivation	Silicon Nitride plus Polyimide			
Wafer Diameter	200 mm			
Max Possible Die Per Wafer	68	36		
Recommended Storage Environment	In original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C			

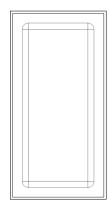


DIODE DIE

V_R = 1200 V



DIE OUTLINE



ORDERING INFORMATION

Device	Inking	Shipping	
PCFF100H120SWF	Yes	Sawn Wafer on Tape	

PCFF100H120SWF

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	1200	V
DC Forward Current, limited by T _{J max} (Note 1)	١ _F	100	А
Pulsed Forward Current, tp limited by T _{J max} (Note 2)	I _{FM}	300	А
Operating Junction Temperature	TJ	-40 to +175	°C
Storage Temperature Range	Tstg	+18 to +28	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Nominal forward current at Tc = 100°C when assembled in power module

2. Not subject to production test - verified by design/characterization.

Reverse Recovery Current

ELECTRICAL CHARACTERISTICS (T_J = $25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit			
STATIC CHARACTERISTICS (Tested on Wafers)										
Breakdown Voltage	V _{BR}	I _R = 1 mA		1200	-	_	V			
Reverse Leakage Current	I _R	V _R = 1200 V		-	-	10	μA			
Forward Voltage	V _F	I _F = 100 A		_	1.78	2.08	V			
ELECTRICAL CHARACTERISTICS (Not subjected to production test - verified by design/characterization)										
Breakdown Voltage	V _{BR}	I _R = 1 mA	$T_J = -40^{\circ}C$	1200	-	-	V			
Forward Voltage	V _F	I _F = 100 A	T _J = 175°C	-	1.9	-	V			
Reverse Recovery Time	T _{rr}	I_F = 100 A, V _R = 600 V, dI _F /dt = 500 A/µs, T _J = 25°C		-	347.1	-	nS			
Reverse Recovery Charge	Q _{rr}			_	4.4	-	μC			
Reverse Recovery Current	I _{RRM}			_	25.8	-	А			
Reverse Recovery Time	T _{rr}	I _F = 100 A, V _R = 600 V, dI _F /dt = 500 A/μs, T _J = 175°C		-	572.2	-	nS			
Reverse Recovery Charge	Q _{rr}			_	12.5	-	μC			

I_{RRM} Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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Α

NOTE: Switching characteristics and thermal properties are depending strongly on module design and mounting technology.

PCFF100H120SWF

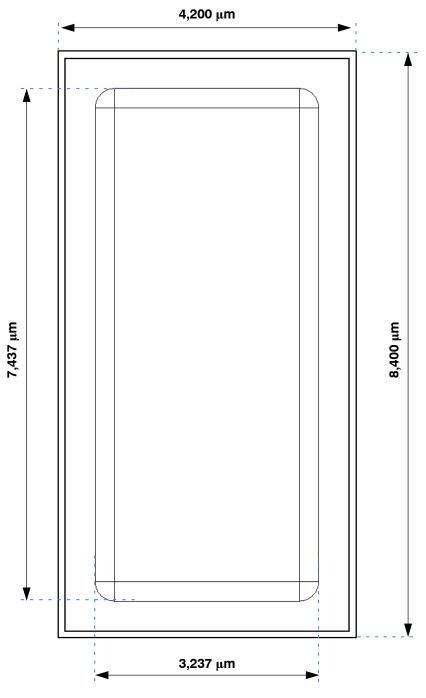


Figure 1. Die Layout

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